

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconducting ceramic which possesses a dielectric strength of 800 V/mm or more and a specific resistance at room temperature of 100 $\Omega \cdot \text{cm}$ or less, the specific resistance at room temperature undergoing substantially no time-course change. The semiconducting ceramic is formed of a sintered semiconducting material containing barium titanate, wherein the average grain size of the semiconducting ceramic is 1.0 μm or less and relative spectral intensity ratio represented by BaCO_3/BaO , which is determined by XPS at the surface of the ceramic, is 0.50 or less.